

- providing a reacting source gas to the wafer; and
- forming a vapor flow through said through-hole to
provide vapor flowing from an upper surface of the susceptor
to a lower surface of the susceptor and thereby preventing
flow of a dopant species from a rear side of the wafer to a
surface of the wafer.

4. (New) A method in accordance with claim 3 wherein
the susceptor further comprises a wafer pocket having a
concave surface for mounting the wafer and wherein the
through-hole passes from the concave surface to the rear
side of the susceptor.

5. (New) The method according to claim 3 further
comprising providing the through-hole on an outer peripheral
side of the wafer.

6. (New) The method according to claim 4 further
comprising providing the through-hole on an outer peripheral
side of the wafer.

R E M A R K S

The present preliminary amendment sets forth the amendments to the claims sought in the captioned reissue divisional application.

In accordance with 37 C.F.R. 1.173(c), the status of the claims are as follows: